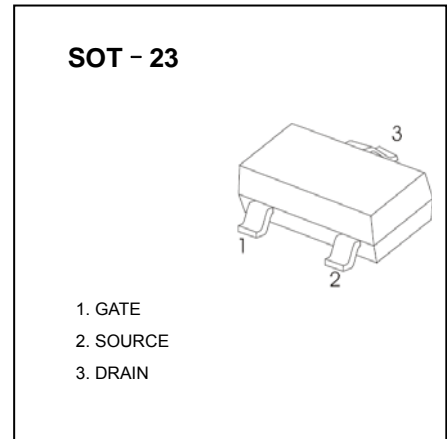
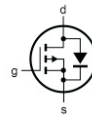
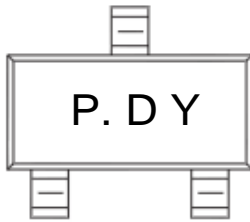


P-Channel Enhancement Mode MOSFET

■ Features

- $V_{DS} (V) = -50V$
- $I_D = -0.13 A$
- $R_{DS(ON)} \leq 10 \Omega$ ($V_{GS} = -5V$)

MARKING



■ Absolute Maximum Ratings $T_a = 25^\circ C$ unless otherwise specified

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	V_{DSS}	-50	V	
Gate-Source Voltage	V_{GSS}	± 20	V	
Drain Current *	I_D	- Continuous	-130	mA
		- Pulsed	-520	
Total Power Dissipation *	P_d	300	mW	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ C/W$	
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ C$	

* Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch;

■ Electrical Characteristics $T_a = 25^\circ C$ unless otherwise specified

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-50			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -50V, V_{GS} = 0V, T_J = 25^\circ C$			-15	μA
		$V_{DS} = -50V, V_{GS} = 0V, T_J = 125^\circ C$			-60	μA
Gate-Body Leakage	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 10	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -1mA$	-0.8		-2.0	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = -5V, I_D = -100mA$			10	Ω
Forward Transconductance	g_{FS}	$V_{DS} = -25V, I_D = -0.1A$	0.05			S
Input Capacitance	C_{iss}	$V_{DS} = -25V, V_{GS} = 0V, f = 1.0MHz$			45	pF
Output Capacitance	C_{oss}				25	pF
Reverse Transfer Capacitance	C_{rss}				12	pF
Turn-On Delay Time	$t_{d(ON)}$	$V_{DD} = -30V, I_D = -0.27A,$		10		ns
Turn-Off Delay Time	$t_{d(OFF)}$	$R_{GEN} = 50\Omega, V_{GS} = -10V$		18		ns